Amendments to th Claims

Claims 1-35 (Canceled).

36. (Original): A semiconductor processing method, comprising:

forming an antireflective coating comprising Ge and Se over a substrate to be patterned;

forming photoresist over the antireflective coating;

exposing the photoresist to actinic radiation effective to pattern the photoresist, the antireflective coating reducing reflection of actinic radiation during the exposing than would otherwise occur under identical conditions in the absence of the antireflective coating;

after the exposing, patterning the substrate through openings in the photoresist and the antireflective coating using the photoresist and the antireflective coating as a mask; and

after patterning the substrate, chemically etching the photoresist and the antireflective coating substantially completely from the substrate using a single etching chemistry.

37. (Original): The method of claim 36 wherein the single etching chemistry is wet.

38. (Original): The method of claim 36 wherein the single etching chemistry is dry.

39. (Original): The method of claim 36 wherein the single etching chemistry is dry and comprises exposure to an oxygen plasma containing atmosphere.

40. (Original): The method of claim 36 wherein the single etching chemistry is dry and comprises exposure to an oxygen plasma containing atmosphere.

41. (Original): The method of claim 36 wherein the antireflective coating consists essentially of Ge and Se.

42. (Currently Amended): The method of claim 36 wherein the antireflective coating consists essentially of about 40 atomic ~~per cent~~ percent Ge and about 60 atomic percent Se.

43. (Original): The method of claim 36 wherein the antireflective coating is substantially amorphous.

44. (Original): The method of claim 36 wherein the antireflective coating comprises at least 30 atomic percent Ge.

45. (Original): The method of claim 36 wherein the antireflective coating comprises from 30 atomic percent to 50 atomic percent Ge.

46. (Original): The method of claim 36 wherein the antireflective coating comprises from 38 atomic percent to 42 atomic percent Ge.

47. (Original): The method of claim 36 wherein the openings in the photoresist and the antireflective coating are formed by solvent processing of the photoresist after the exposing to form the photoresist openings, followed by dry etching of the antireflective coating through the photoresist openings.

48. (Original): The method of claim 47 wherein forming the openings in the antireflective coating comprises after said exposing, exposing the antireflective coating through the photoresist to radiation having a wavelength from about 190 nanometers to about 450 nanometers, and thereafter dry etching the antireflective coating in an oxygen comprising ambient.